Abstracts

High-power GaN MESFET on sapphire substrate

C. Gaquiere, S. Trassaert, B. Boudart and Y. Crosnier. "High-power GaN MESFET on sapphire substrate." 2000 Microwave and Guided Wave Letters 10.1 (Jan. 2000 [MGWL]): 19-20.

The first power results of GaN MESFET achieved at 2 GHz are presented. A power density of 2.2 W/mm has been obtained with an associated power added efficiency of 27% at V/sub ds/=30 V and V/sub gs/=-2 V. These results represent a significant improvement over similar MESFET's or HFET's grown on GaAs or InP substrates.

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